

2.7x2.4 mm Silicon PD Chip datasheet

P/N : WS43-01B

Application

Si PIN photodiode chip

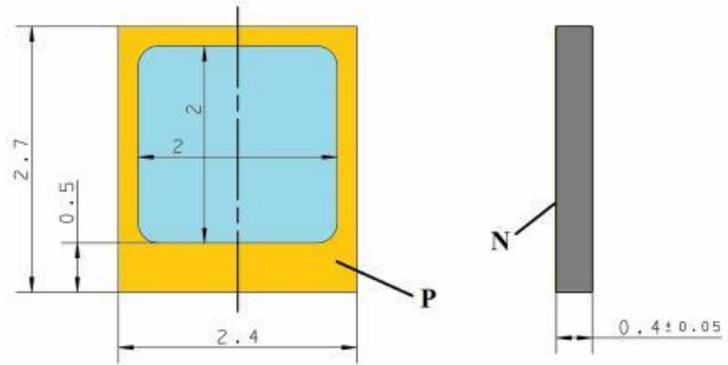
Structure

Planar type : PIN diode

Electrodes :

Back side (Cathode) : Au Alloy

Top side (Anode) : Au



DIMENSIONS

Conditions	Min	Typ.	Max	Unit
Active	2000±30 x 2000±30			μm
Chip width	2400±30			μm
Chip length	2700±30			μm
Chip height	350	400	450	μm

Electro-Optical Characteristics (@ Ta =25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=5mA, H=0	0.6		0.9	V
Reverse Dark Current	Id	Vr=10V			50	nA
Responsivity	Re.	VR=10V, λ=795nm		0.52		A/W
Sensitive Wavelength Range	λ		400		1100	nm
Capacitance	Cj	VR=10V, f=1MHz			15	pF